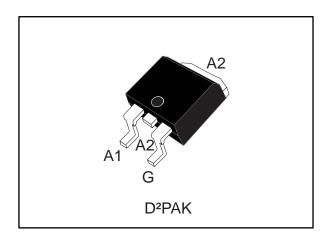


# 12 A Snubberless™ Triac

Datasheet -production data



### **Features**

- High static dV/dt
- High dynamic turn-off commutation (dl/dt)c
- 150 °C maximum T<sub>i</sub>
- Three quadrants
- Surge capability V<sub>DSM</sub>, V<sub>RSM</sub> = 900 V

#### **Benefits**

- High immunity to turn-on thanks to high static dV/dt
- Better turn-off in high temperature environments thanks to (dl/dt)c
- Increase of thermal margin due to extended working T<sub>j</sub> up to 150 °C
- Good thermal resistance due to non-insulated tab

### **Applications**

- General purpose AC line load switching
- Motor control circuits
- Home appliances
- Heating
- Lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

### **Description**

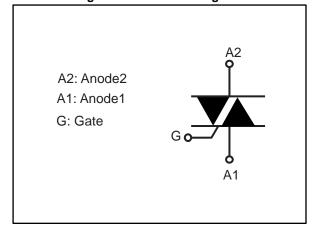
Available in SMD, the T1235T-8G Triac can be used for the on/off or phase angle control function in general purpose AC switching where high commutation capability is required. This device can be used without a snubber RC circuit when the limits defined are respected.

D<sup>2</sup>PAK package is UL94-V0 flammability resin compliance.

Package environmentally friendly Ecopack<sup>®</sup>2 graded (RoHS and Halogen Free compliance).

Snubberless™ is a trademark of STMicroelectronics.

Figure 1: Functional diagram



**Table 1: Device summary** 

Symbol	Value	Unit
I <sub>T(RMS)</sub>	12	Α
V <sub>DRM</sub> /V <sub>RRM</sub>	800	V
V <sub>DSM</sub> /V <sub>RSM</sub>	900	V
I <sub>GT</sub>	35	mA

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Characteristics T1235T-8G

## 1 Characteristics

Table 2: Absolute maximum ratings (limiting values)

Symbol	Parame	Value	Unit		
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave	<del>)</del> )	T <sub>c</sub> = 124 °C	12	Α
l-a	Non repetitive surge peak on-state current,		$t_p = 16.7 \text{ ms}$	95	Α
I <sub>TSM</sub>	T <sub>j</sub> initial = 25 °C		$t_p = 20 \text{ ms}$	90	A
l <sup>2</sup> t	I <sup>2</sup> t value for fusing		T <sub>j</sub> initial = 25 °C	54	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state currer $I_G = 2 \times I_{GT}$ , tr $\leq 100 \text{ ns}$	f = 100 Hz	100	A/µs	
\/\/\/	V <sub>DRM</sub> /V <sub>RRM</sub> Repetitive peak off-state voltage		T <sub>j</sub> = 150 °C	600	V
V DRM/ V RRM			T <sub>j</sub> = 125 °C	800	V
V <sub>DSM</sub> /V <sub>RSM</sub>	Non Repetitive peak off-state voltag	$t_p = 10 \text{ ms}$	900	V	
I <sub>GM</sub>	Peak gate current	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 150 °C	4	Α
P <sub>G(AV)</sub>	Average gate power dissipation	T <sub>j</sub> = 150 °C	1	W	
T <sub>stg</sub>	Storage junction temperature range		-40 to +150	°C	
Tj	Operating junction temperature range			-40 to +150	°C

Table 3: Electrical characteristics ( $T_j = 25$  °C, unless otherwise specified)

Symbol	Test conditions	Quadrants; T <sub>j</sub>		Value	Unit
1	$V_D = 12 \text{ V}, \text{ R}_L = 33 \Omega$	1 - 11 - 111	Min.	1.75	mA
I <sub>GT</sub>	$V_D = 12 \text{ V}, R_L = 33 \Omega$	1 - 11 - 111	Max.	35	mA
V <sub>G</sub> T	$V_D = 12 \text{ V}, \text{ R}_L = 33 \Omega$	1 - 11 - 111	Max.	1.3	V
$V_{GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 150 \text{ °C}$	1 - 11 - 111	Min.	0.2	V
IL	I <sub>G</sub> = 1.2 x I <sub>GT</sub>	I - III	Max.	60	mA
IL	I <sub>G</sub> = 1.2 x I <sub>GT</sub>	II	Max.	80	mA
IH <sup>(1)</sup>	I <sub>T</sub> = 500 mA, gate open		Max.	40	mA
dV/dt (1)	V <sub>D</sub> = 536 V, gate open	T <sub>j</sub> = 125 °C	Min.	2000	V/µs
av/at (7	V <sub>D</sub> = 402 V, gate open	T <sub>j</sub> = 150 °C	Min.	1000	V/µs
(dl/dt)c <sup>(1)</sup>	Without anulhor (d)/(dt) > 20 )//us	T <sub>j</sub> = 125 °C	Min.	12	A/ms
	Without snubber, (dV/dt)c > 20 V/μs	T <sub>j</sub> = 150 °C	Min.	6	A/ms

#### Notes

<sup>&</sup>lt;sup>(1)</sup>For both polarities of A2 referenced to A1.

T1235T-8G Characteristics

**Table 4: Static characteristics** 

Symbol	Test conditions	Tj		Value	Unit
V <sub>TM</sub> <sup>(1)</sup>	$I_T = 17 \text{ A}, t_p = 380  \mu\text{s}$	25 °C	Max.	1.6	٧
V <sub>TO</sub> <sup>(1)</sup>	Threshold on-state voltage	150 °C	Max.	0.85	٧
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	150 °C	Max.	50	mΩ
	V <sub>DRM</sub> = V <sub>RRM</sub> = 800 V	25 °C	Max.	5	μΑ
I <sub>DRM</sub> /I <sub>RRM</sub>	VDRM = VRRM = 800 V	125°C	iviax.	1	mA
	$V_{DRM} = V_{RRM} = 600 \text{ V}$	150 °C	Max.	3.1	mA

### Notes:

**Table 5: Thermal resistance** 

Symbol	Parameter			Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)	D²PAK	Max.	1.6	°C/W

 $<sup>^{(1)}</sup>$ For both polarities of A2 referenced to A1.

Characteristics T1235T-8G

# 1.1 Characteristics (curves)

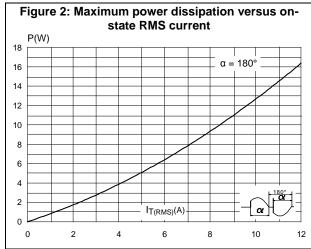
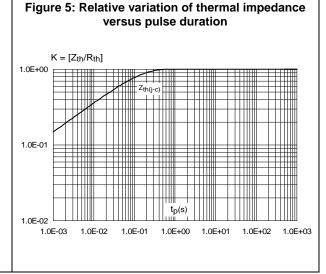
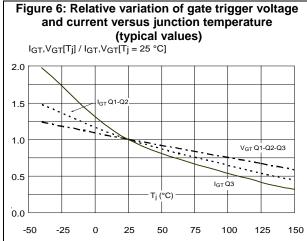
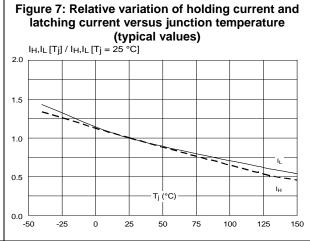


Figure 4: On-state RMS current versus ambient temperature (free air convection) I<sub>T(RMS)</sub>(A) 4.0 3.5 D<sup>2</sup>PAK 3.0 Scu = 1 cm<sup>2</sup> Epoxy PCB FR4 copper thickness = 35 μm 2.5 2.0 15 1.0 0.5 T<sub>a</sub>(°C) 0.0 25

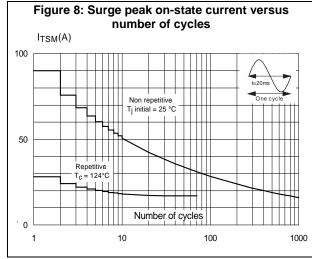






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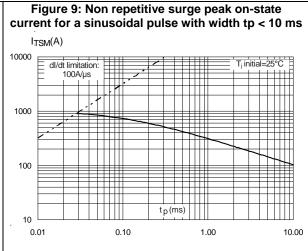
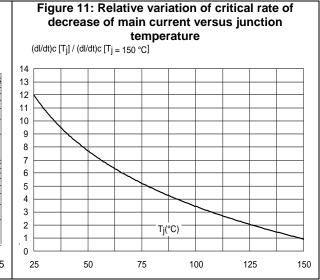
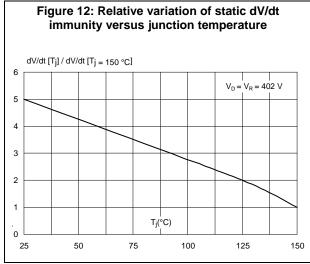
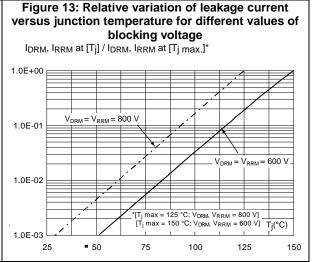


Figure 10: On-state characteristics (maximum values)  $|T_{TM}(A)|$   $|T_{TM}(A)|$  |T









Package information T1235T-8G

## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- ECOPACK®2 compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

## 2.1 D<sup>2</sup>PAK package information

Max resin gate protrusion: 0.5 mm (1)

A1

A2

A3

Gauge Plane

(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

Figure 14: D<sup>2</sup>PAK package outline

T1235T-8G Package information

Table 6: D<sup>2</sup>PAK package mechanical data

	Dimensions					
Ref.		Millimeters			Inches <sup>(1)</sup>	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
А3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
С	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
е	2.54			0.1		
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
Н	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.27		1.40	0.0500		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

### Notes:

 $<sup>\</sup>ensuremath{^{(1)}}\mbox{Dimensions}$  in inches are given for reference only

Package information T1235T-8G

Figure 15: D<sup>2</sup>PAK recommended footprint (dimensions are in mm)

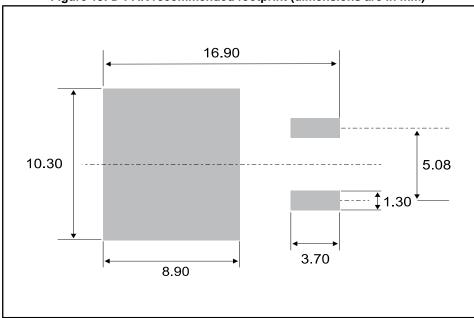
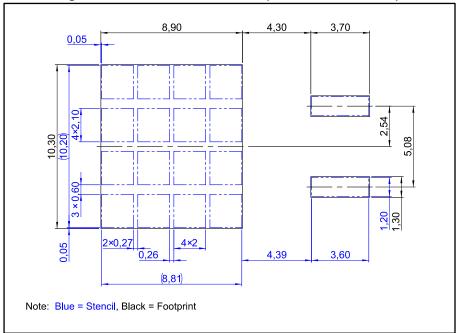


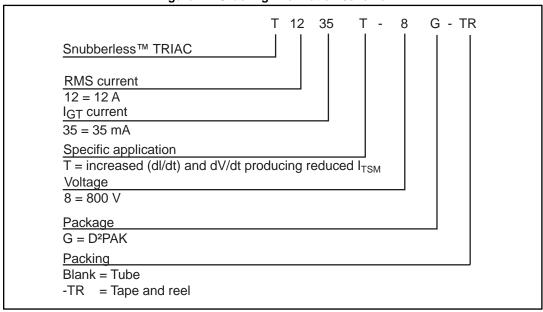
Figure 16: D<sup>2</sup>PAK stencil definitions (dimensions are in mm)



T1235T-8G Ordering information

# 3 Ordering information

Figure 17: Ordering information scheme



**Table 7: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T1235T-8G-TR	T4005T 0C	D²PAK	1 20 ~	1000	Tape and reel
T1235T-8G	T1235T-8G	D-PAK	1.38 g	50	Tube

# 4 Revision history

**Table 8: Document revision history** 

Date	Revision	Changes
19-Dec-2017	1	Initial release.

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